

ETCHING METHOD AND ETCHING APPARATUS

ABSTRACT

A technique increases verticality in etching. An etching method is a method for etching a
5 target film with a plasma processing apparatus including a chamber and a substrate support in
the chamber to support a substrate. The etching method includes placing a substrate including
the target film on the substrate support, supplying a process gas containing an HF gas into the
chamber, generating plasma from the process gas in the chamber with radio-frequency power
having a first frequency, and applying a pulsed voltage periodically to the substrate support at
10 a second frequency lower than the first frequency.

Fig. 4